## NSN 5961-00-411-1288



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-00-411-1288 **Inclosure Material:** Metal **Overall Length:** 0.320 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: T0-60 **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 65.0 breakdown voltage, collector-to-base, emitter open and 4.0 breakdown voltage, collector-to-emitter, base open and 40.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 1.50 amperes source cutoff current and 200.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 11.0 watts small-signal input power, common-collector **Transfer Ratio:** 150.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 pin Shelf Life: N/a

No

**Unit Of Measure:** 

Demilitarization:

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